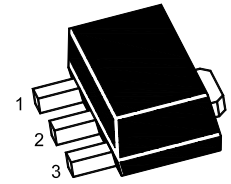


2SB1561U

PNP Silicon Epitaxial Planar Power Transistor

Medium Power Transistor



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CB0}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	60	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current - DC Collector Current - Pulse ¹⁾	$-I_C$ $-I_{CP}$	2 6	A
Total Power Dissipation	P_{tot}	0.5 ²⁾ 2 ³⁾	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

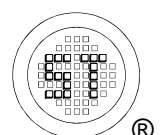
¹⁾ Single pulse, $P_w = 10$ ms

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	250 ²⁾ 62.5 ³⁾	$^\circ\text{C/W}$

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

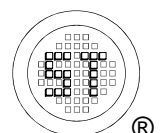
²⁾ When mounted on a 40 x 40 x 0.7 mm ceramic board



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Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 0.5\text{ A}$ at $-V_{CE} = 2\text{ V}$, $-I_C = 1.5\text{ A}$	h_{FE} h_{FE}	120 45	- -	270 -	- -
Collector Base Breakdown Voltage at $-I_C = 50\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	60	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 50\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	-	0.1	μA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	0.1	μA
Collector Emitter Saturation Voltage at $-I_C = 1\text{ A}$, $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.35	V
Transition Frequency at $-V_{CE} = 2\text{ V}$, $I_E = 0.5\text{ A}$, $f = 100\text{ MHz}$	f_T	-	200	-	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	23	-	pF



Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

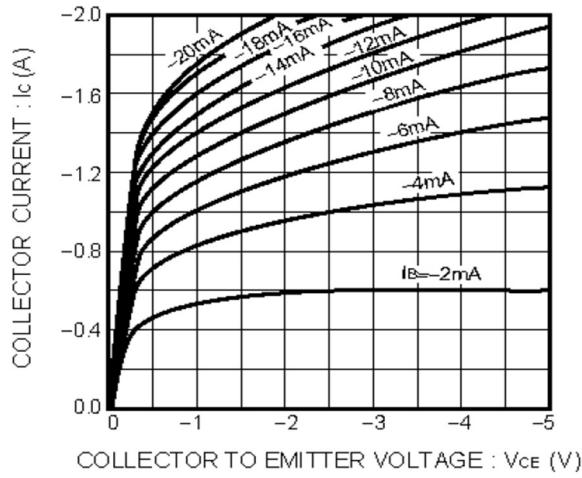


Fig. 2 Collector Current vs. Base to Emitter Voltage

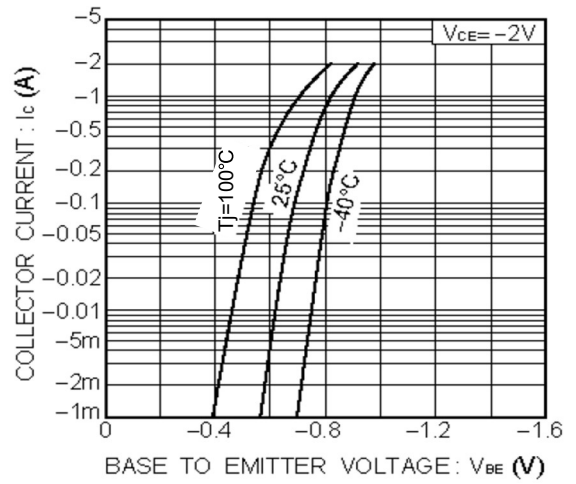


Fig. 3 DC Current Gain vs. Collector Current

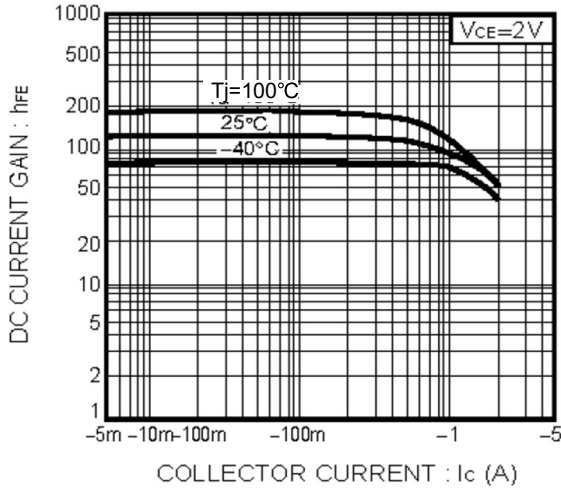


Fig. 4 DC Current Gain vs. Collector Current

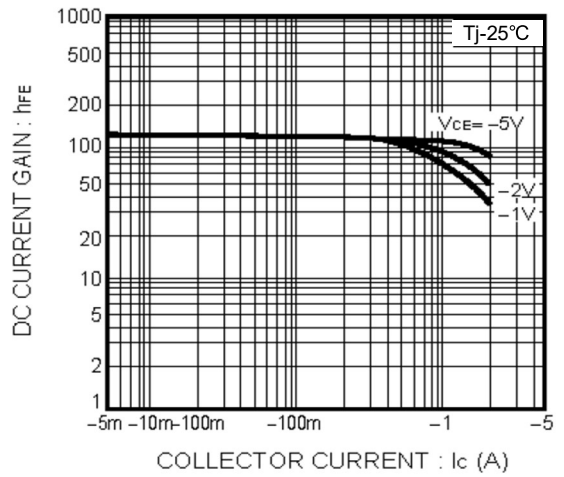


Fig. 5 VCESAT vs. Collector Current

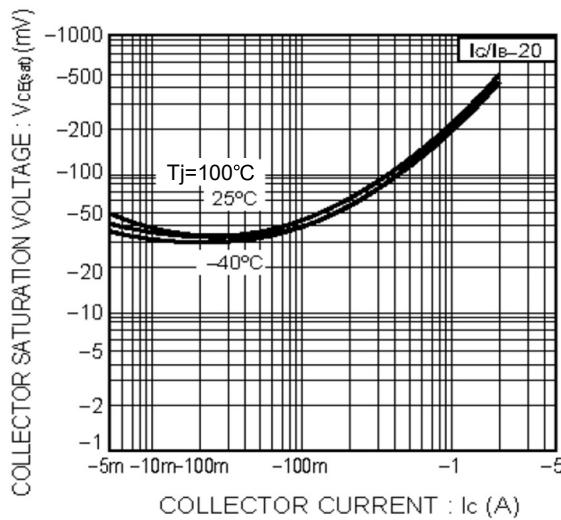
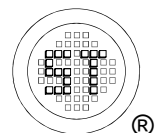
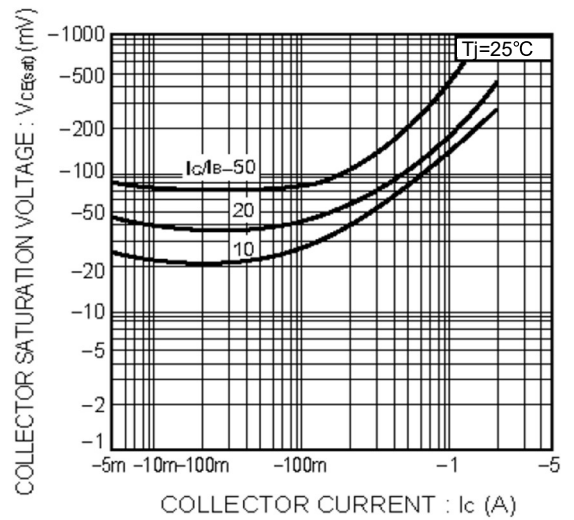


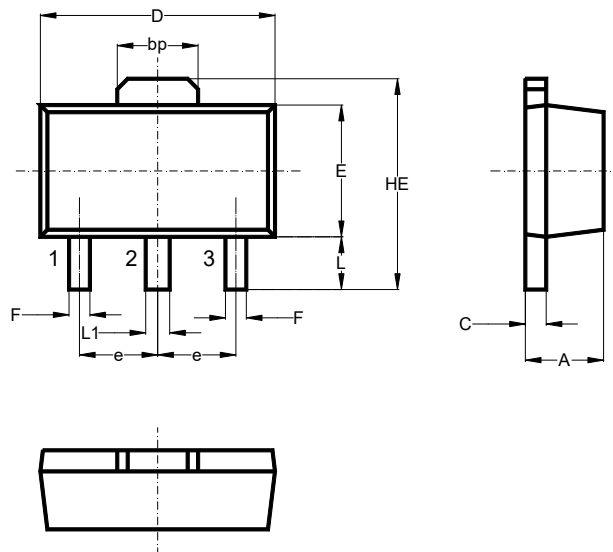
Fig. 6 VCESAT vs. Collector Current



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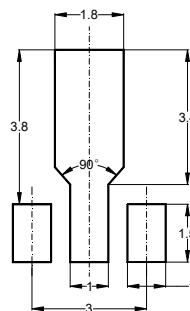
Package Outline (Dimensions in mm)

SOT-89



Unit	A	bp	C	D	E	F	HE	e	L	L1
mm	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

Recommended Soldering Footprint

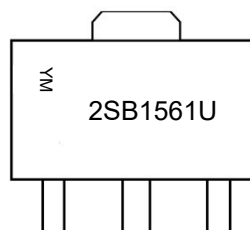


Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-89	12	8 ± 0.1	0.315 ± 0.004	178	7	1,000
				330	13	4,000

Marking information

- " 2SB1561U " = Part No.
- "YM" = Date Code Marking
- "Y" = Year
- "M" = Month
- Font type: Arial



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